

RJK6022DJE

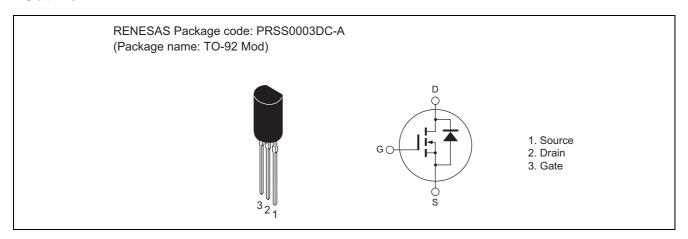
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1484-0600 Rev.6.00 Nov 10, 2006

Features

- Low on-resistance
- Low drive current
- High density mounting

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit	
Drain to source voltage	V_{DSS}	600	V	
Gate to source voltage	V_{GSS}	±30	V	
Drain current	I _D	0.2	А	
Drain peak current	I _{D (pulse)} Note1	0.8	А	
Body-drain diode reverse drain current	I _{DR}	0.2	А	
Body-drain diode reverse drain peak current	I _{DR} (pulse)	0.8	А	
Channel dissipation	Pch	0.9	W	
Channel to ambient thermal impedance	$ heta_{ch-a}$	139	°C/W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

Electrical Characteristics

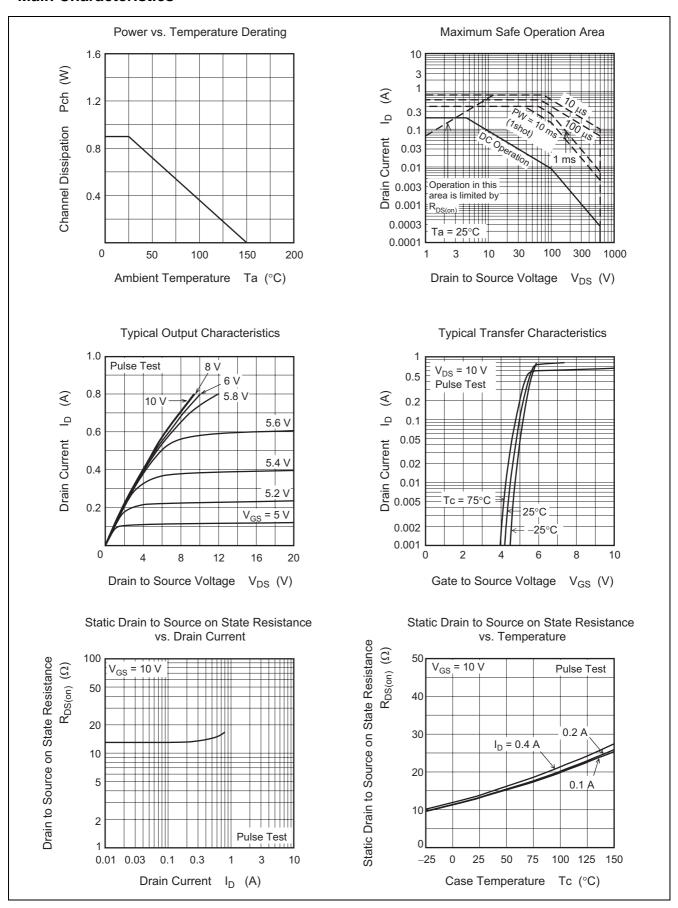
 $(Ta = 25^{\circ}C)$

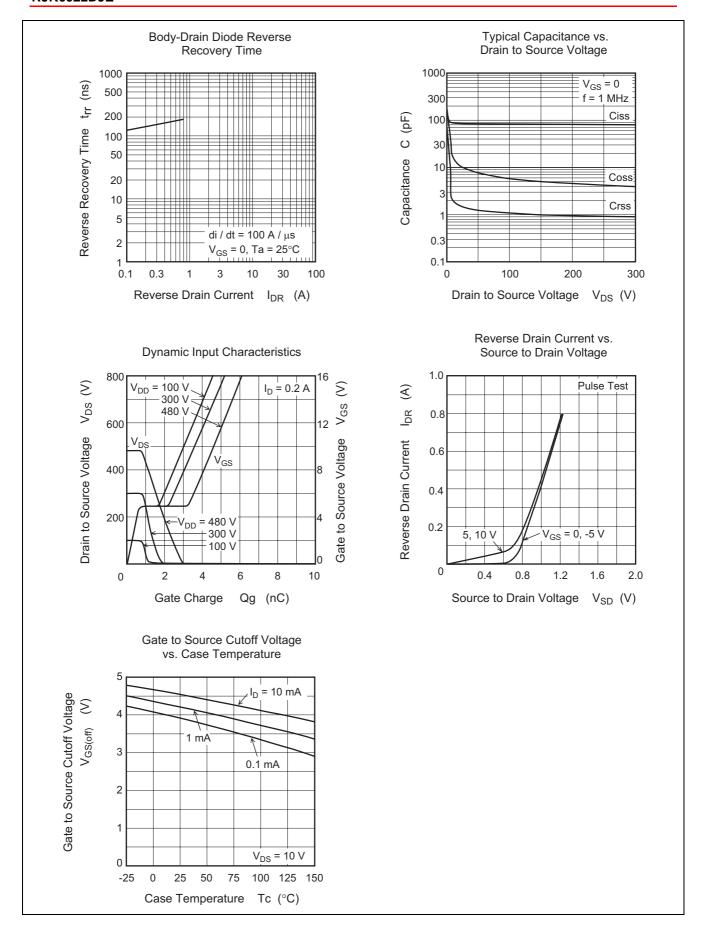
Item	Symbol	Min	Тур	Max	Unit	Test conditions	
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$	
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$	
Gate to source cutoff voltage	$V_{GS(off)}$	3	_	5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	
Static drain to source on state resistance	R _{DS(on)}	_	13	15	Ω	$I_D = 0.1 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note2}}$	
Input capacitance	Ciss	_	84	_	pF	V _{DS} = 25 V	
Output capacitance	Coss	_	11	_	pF	$V_{GS} = 0$	
Reverse transfer capacitance	Crss	_	2	_	pF	f = 1 MHz	
Turn-on delay time	t _{d(on)}	_	31	_	ns	$I_D = 0.1 A$	
Rise time	t _r	_	14	_	ns	V _{GS} = 10 V	
Turn-off delay time	$t_{d(off)}$	_	53	_	ns	$R_L = 3000 \Omega$	
Fall time	t _f	_	173	_	ns	$Rg = 10 \Omega$	
Total gate charge	Qg	_	4.5	_	nC	V _{DD} = 480 V	
Gate to source charge	Qgs	_	0.6	_	nC	$V_{GS} = 10 \text{ V}$	
Gate to drain charge	Qgd	_	2.6	_	nC	$I_D = 0.2 A$	
Body-drain diode forward voltage	V_{DF}	_	0.77	1.25	V	$I_F = 0.2 \text{ A}, V_{GS} = 0^{\text{Note2}}$	
Body-drain diode reverse recovery time	t _{rr}	_	150	_	ns	$I_F = 0.2 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$	

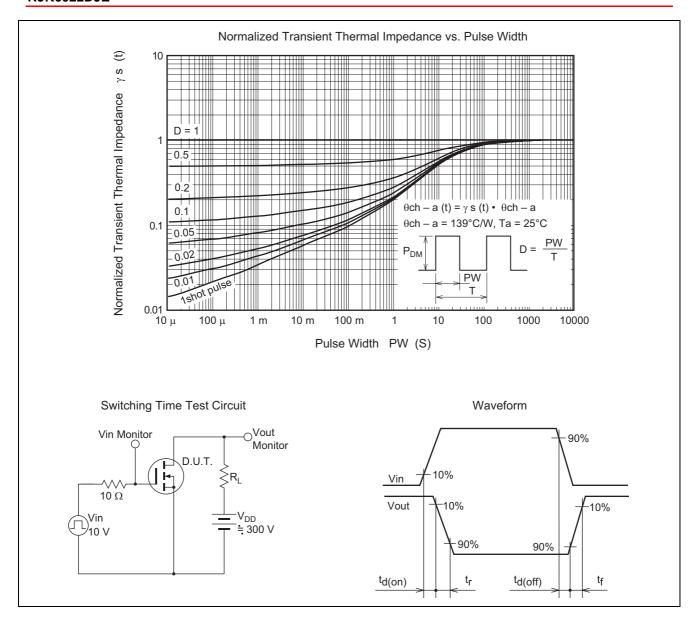
Notes: 2. Pulse test

^{3.} Since this device is equipped with high voltage FET chip ($V_{DSS} \ge 600 \text{ V}$), high voltage may be supplied. Therefore, please be sure to confirm about Electric discharge between Drain terminal and other terminal.

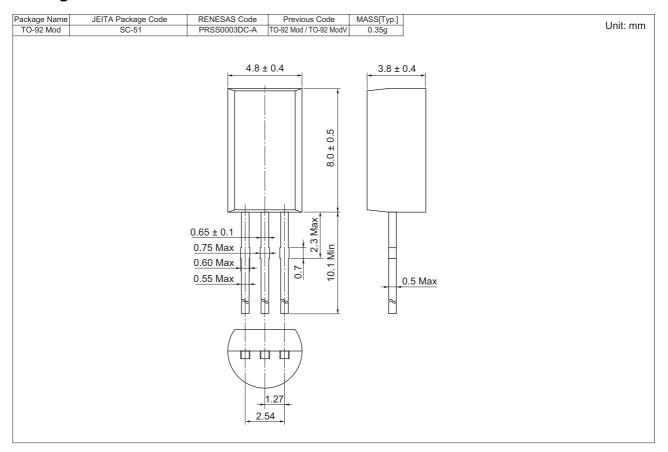
Main Characteristics







Package Dimensions



Since RJK6022DJE is equipped with high voltage FET chip ($V_{DSS} \ge 600 \text{ V}$), high voltage may be supplied. Therefore, please be sure to confirm about Electric discharge between Drain terminal and other terminal.

Ordering Information

Part Name	Quantity	Shipping Container
RJK6022DJE-00-Z0	2500 pcs	Hold Box, Radial Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510